



Phase Control Thyristor

DS5829-5 February 2014 (LN31341)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR780G42 DCR780G40 DCR780G38	4200 4000 3800	$\begin{split} &T_{\nu j} = \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ &I_{DRM} = I_{RRM} = \text{100mA}, \\ &V_{DRM}, V_{RRM} \ t_p = \text{10ms}, \\ &V_{DSM} \& V_{RSM} = \\ &V_{DRM} \& V_{RRM} + \text{100V} \\ &\text{respectively} \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR780G42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	4200V
I _{T(AV)}	780A
I _{TSM}	10500A
dV/dt*	1500V/µs
dI/dt	400A/us

* Higher dV/dt selections available

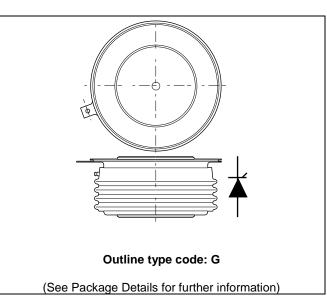


Fig. 1 Package outline



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	780	А
I _{T(RMS)}	RMS value	-	1225	А
I _T	Continuous (direct) on-state current	-	1173	А

SURGE RATINGS

Symbol Parameter		Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	10.5	kA
I ² t I ² t for fusing		$V_R = 0$	0.55	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	s	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.0268	°C/W
		Single side cooled	Anode DC	-	0.0527	°C/W
			Cathode DC	-	0.0652	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 11.5kN	Double side	-	0.0072	°C/W
		(with mounting compound)	Single side	-	.0144	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			10	13	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	100	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)}	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω,	Non-repetitive	-	400	A/µs
		$t_r < 0.5 \mu s, T_j = 125^{\circ}C$				
$V_{T(TO)}$	Threshold voltage – Low level	100A to 500A at T _{case} = 125°	С	-	.87	V
	Threshold voltage – High level	500A to 3000A at T _{case} = 125°C		-	1.053	V
r _T	On-state slope resistance – Low level	100A to 500A at T _{case} = 125°C		-	1.2244	mΩ
	On-state slope resistance – High level	500A to 3000A at T _{case} = 125°C		-	0.8443	mΩ
t _{gd}	Delay time	$V_D = 67\% \ V_{DRM}$, gate source 30V, 10Ω		TBD	TBD	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 200$ V, dl/dt	= 5A/μs,	300	600	μs
		dV _{DR} /dt = 20V/μs linear				
Qs	Stored charge	$I_T = 2000A$, $T_j = 125$ °C, $dI/dt = 5A/\mu s$,		1100	2200	μC
اد	Latching current	$T_j = 25$ °C, $V_D = 5V$		-	3	А
I _H	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500$	0A, I _T = 5A	-	300	mA



GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol Parameter		Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25$ °C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

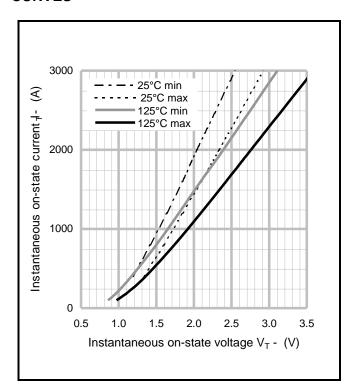


Fig.2 Maximum & minimum on-state characteristics

these values are valid for $T_j = 125$ °C for $I_T 50A$ to 3000A



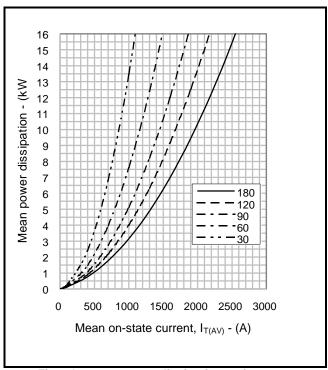


Fig.3 On-state power dissipation – sine wave

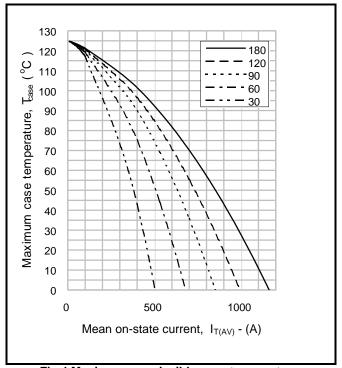


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

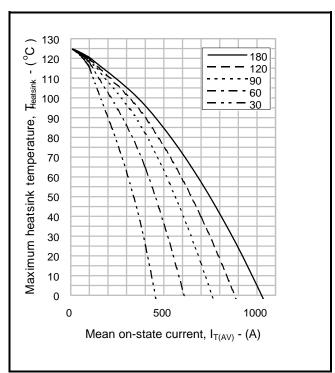


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

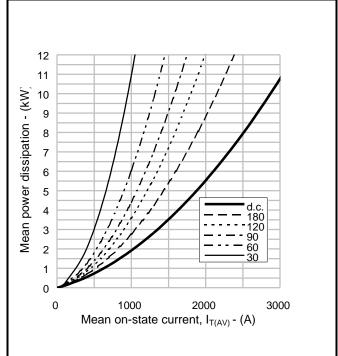
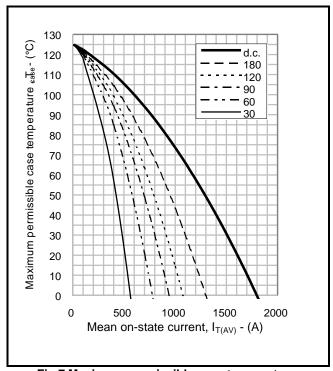
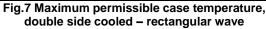


Fig.6 On-state power dissipation - rectangular wave







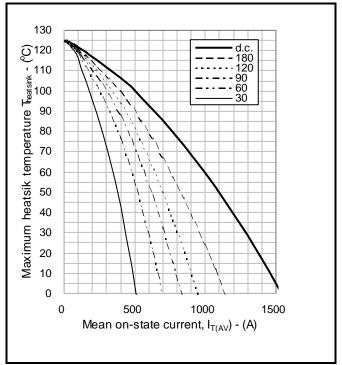
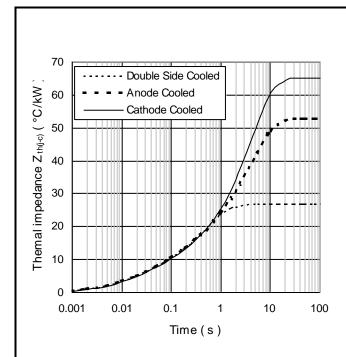


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave



		1	2	3	4
Double side cooled	R _i (°C/kW)	2.2995	5.4226	16.9074	2.1488
	T _i (s)	0.0066401	0.0457025	0.4962482	1.8248
Anode side cooled	R _i (°C/kW)	2.3214	5.2661	10.2686	34.8031
	T _i (s)	0.0066948	0.045528	0.3484209	4.582
Cathode side cooled	R _i (°C/kW)	2.4895	5.9105	7.4256	49.3432
	T. (s)	0.0070404	0.052805	U 30330U3	4 2205

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(-T/T_i))]$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance $R_{\text{th}(j\text{-}c)}$ when the device operates at conduction angles other than d.c.

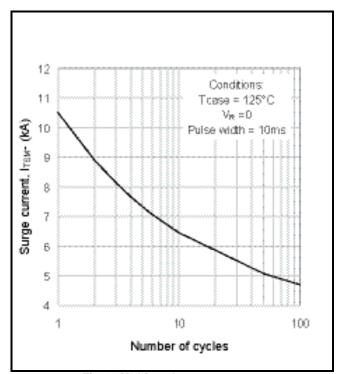
Double side cooling			
	ΔZ_{th} (z)	
θ°	sine.	rect.	θ
180	4.15	2.72	18
120	4.90	4.02	12
90	5.74	4.79	Ō
60	6.53	5.65	6
30	7.16	6.64	3
15	7.46	7 10	1

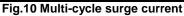
L		Anode Side (Cooling	L	Ca	thode Sided	1 (
		ΔZ_t	_h (z)			ΔZ_{ti}	۱ (
	θ°	sine.	rect.		θ°	sine.	
	180	4.15	2.72		180	4.13	
	120	4.89	4.02		120	4.87	
	90	5.73	4.78		90	5.69	
	60	6.52	5.65		60	6.46	
	30	7.15	6.62		30	7.07	
	15	7.44	7.16		15	7.36	

Ca	thode Sided	d Cooling
	ΔZ_{ti}	1 (z)
θ°	sine.	rect.
180	4.13	2.71
120	4.87	4.00
90	5.69	4.76
60	6.46	5.60
30	7.07	6.56

Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)







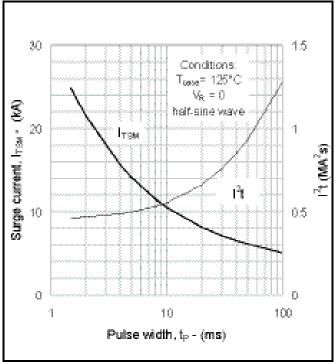


Fig.11 Single-cycle surge current

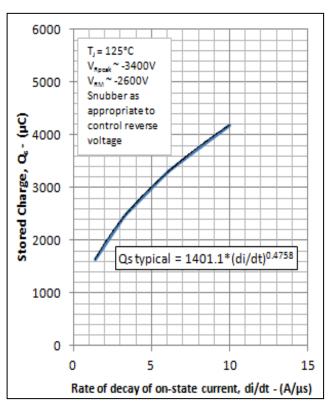


Fig.12 Stored Charge vs di/dt

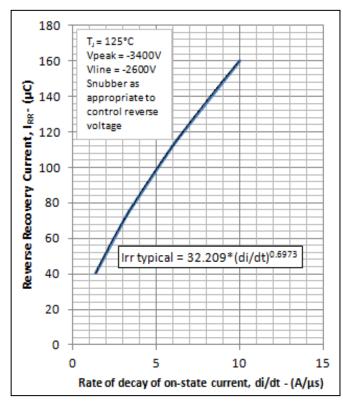


Fig.13 Reverse Recorvery Current vs di/dt

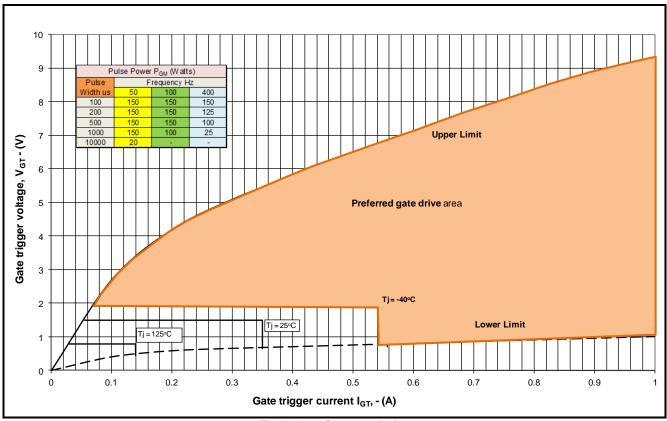


Fig14 Gate Characteristics

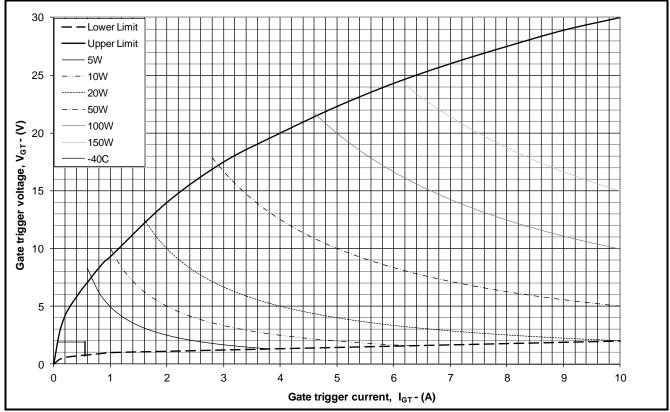


Fig. 15 Gate characteristics



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

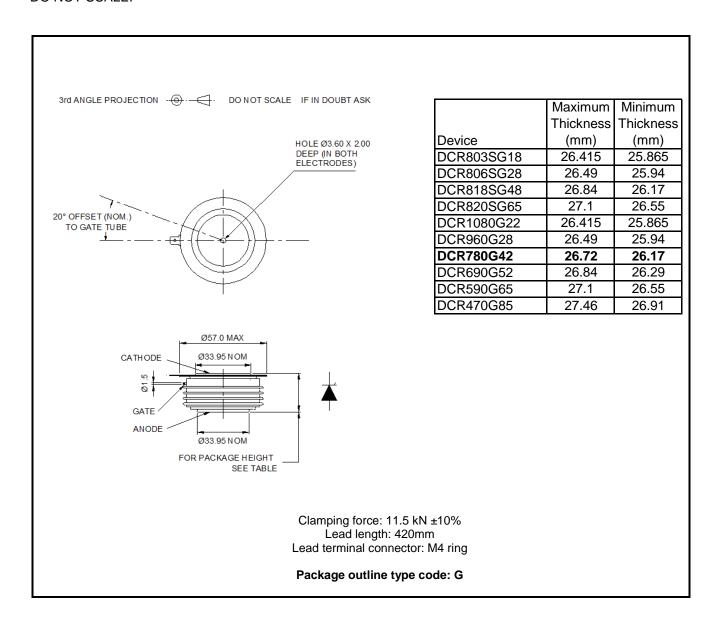


Fig.16 Package outline





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